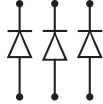
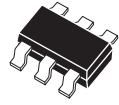


**CMXSH-3**

**SURFACE MOUNT  
SUPERmini™  
TRIPLE ISOLATED  
SILICON SCHOTTKY  
DIODES**

**SUPERmini™**



**SOT-26 CASE**

**Central™**  
**Semiconductor Corp.**

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CMXSH-3 type contains three (3) Isolated Schottky Silicon Switching Diodes, manufactured by the epitaxial planar process, epoxy molded in a SUPERmini™ surface mount package, designed for applications requiring low forward voltage drop.

**MARKING CODE: XH3**

**MAXIMUM RATINGS** ( $T_A=25^\circ\text{C}$ )

Peak Repetitive Reverse Voltage  
Continuous Forward Current  
Peak Repetitive Forward Current  
Forward Surge Current,  $t_p=10$  ms  
Power Dissipation  
Operating and Storage  
Junction Temperature  
Thermal Resistance

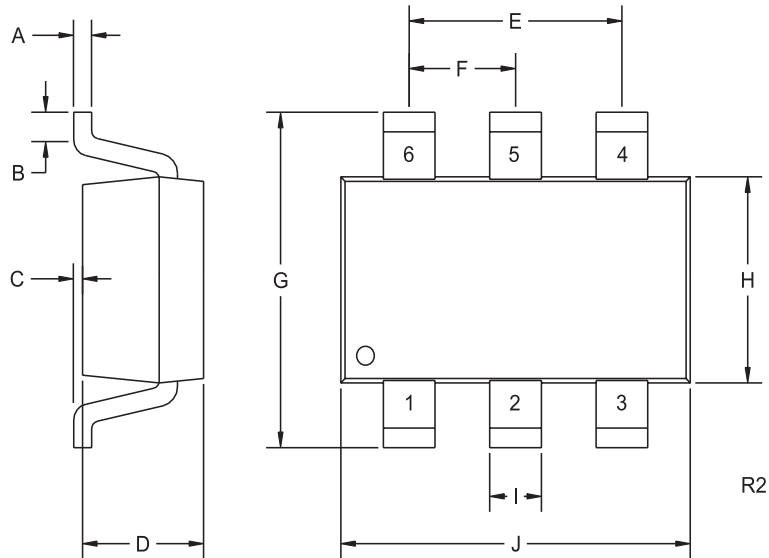
SYMBOL		UNITS
$V_{RRM}$	30	V
$I_F$	100	mA
$I_{FRM}$	350	mA
$I_{FSM}$	750	mA
$P_D$	350	mW
$T_J, T_{stg}$	-65 to +150	$^\circ\text{C}$
$\theta_{JA}$	357	$^\circ\text{C/W}$

**ELECTRICAL CHARACTERISTICS PER DIODE** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

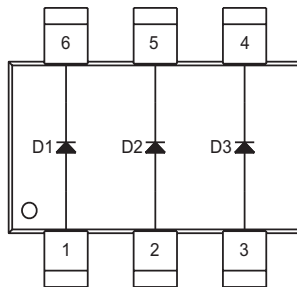
SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
$I_R$	$V_R=25\text{V}$		90	500	nA
$I_R$	$V_R=25\text{V}, T_A=100^\circ\text{C}$		25	100	$\mu\text{A}$
$BV_R$	$I_R=100\mu\text{A}$	30			V
$V_F$	$I_F=2.0\text{mA}$		0.29	0.33	V
$V_F$	$I_F=15\text{mA}$		0.40	0.45	V
$V_F$	$I_F=100\text{mA}$		0.74	1.00	V
$C_T$	$V_R=1.0\text{V}, f=1.0\text{MHz}$		7.0		pF
$t_{rr}$	$I_F=I_R=10\text{mA}, I_{rr}=1.0\text{mA}, R_L=100\Omega$			5.0	ns

R4 (3-June 2005)

**SOT-26 CASE - MECHANICAL OUTLINE**



**Pin Configuration**



**LEAD CODE**

- 1) ANODE D1
- 2) ANODE D2
- 3) ANODE D3
- 4) CATHODE D3
- 5) CATHODE D2
- 6) CATHODE D1

**MARKING CODE: XH3**

SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.007	0.11	0.19
B	0.016	-	0.40	-
C	-	0.004	-	0.10
D	0.039	0.047	1.00	1.20
E	0.074	0.075	1.88	1.92
F	0.037	0.038	0.93	0.97
G	0.102	0.118	2.60	3.00
H	0.059	0.067	1.50	1.70
I	0.016		0.41	
J	0.110	0.118	2.80	3.00

SOT-26 (REV: R2)